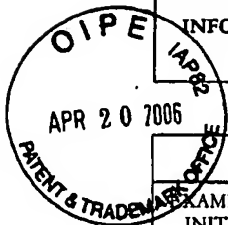


Form 1449*	Docket Number: G&C 30794.94-US-WO	Application Number: 10/537,385
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION		
Applicant: Benjamin A. Haskell et al.		
Filing Date: June 3, 2005	Group Art Unit: 2841 2824	



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	Applicant: Benjamin A. Haskell et al.	
	Filing Date: June 3, 2005	Group Art Unit: 2014 2824

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	Applicant: Benjamin A. Haskell et al.	
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Form 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Docket Number: G&C 30794.94-US-WO	Application Number: 10/537,385
	Applicant: Benjamin A. Haskell et al.	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10537385
	Filing Date		2005-06-03
	First Named Inventor	Benjamin A. Haskell et al.	
	Art Unit	2841 2824	
	Examiner Name	Steven Ho Yin Lok Michael Lulis	
	Attorney Docket Number		

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Application Number	10537385
Filing Date	2005-06-03
First Named Inventor	Benjamin A. Haskell et al.
Art Unit	2844 2824
Examiner Name	Steven Ho Yin Lok Michael Lulis
Attorney Docket Number	

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Examiner Signature	/Michael Lulis/	Date Considered	06/21/2007
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Date Mailed: January 15, 2007

Sheet 1 of 1

Form 1449*	Docket Number: GAC 30794.94-US-WO	Application Number: 10/537,385
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Applicant: Benjamin A. Haskell et al.	
	Filing Date: June 3, 2005	Group Art Unit: 2044 2824

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Form 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Docket Number: G&C 30794.94-US-WO		Application Number: 10/537,385	
	Applicant: Benjamin A. Haskell et al.			
	Filing Date: June 3, 2005		Group Art Unit: 2844 2824	

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EXAMINER: /Michael Lulis/	DATE CONSIDERED: 06/21/2007
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